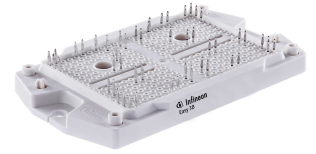


EasyPACK™ module with TRENCHSTOP™ IGBT7 and emitter controlled 7 diode and PressFIT / NTC

Features

- Electrical features
 - $V_{CES} = 1200\text{ V}$
 - $I_{C\text{nom}} = 200\text{ A} / I_{CRM} = 400\text{ A}$
 - Low $V_{CE,\text{sat}}$
 - Overload operation up to 175°C
 - TRENCHSTOP™ IGBT7
- Mechanical features
 - Al_2O_3 substrate with low thermal resistance
 - Copper base plate
 - High power and thermal cycling capability
 - Integrated NTC temperature sensor
 - PressFIT contact technology



Potential applications

- Motor drives
- Servo drives
- Auxiliary inverters

Product validation

- Qualified for industrial applications according to the relevant tests of IEC 60747, 60749 and 60068

Description

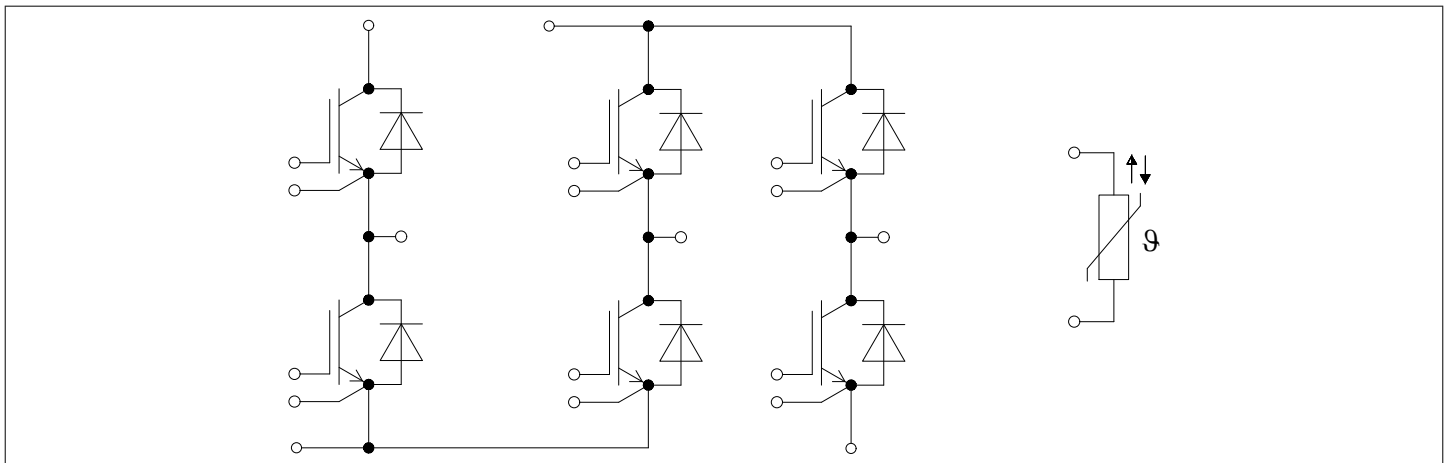


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1 Package

Table 1 Insulation coordination

Parameter	Symbol	Note or test condition	Values	Unit
Isolation test voltage	V_{ISOL}	RMS, $f = 50 \text{ Hz}$, $t = 1 \text{ min}$	2.5	kV
Internal isolation		basic insulation (class 1, IEC 61140)	Al_2O_3	
Creepage distance	d_{Creep}	terminal to heatsink	11.2	mm
Creepage distance	d_{Creep}	terminal to terminal	6.8	mm
Clearance	d_{Clear}	terminal to heatsink	9.4	mm
Clearance	d_{Clear}	terminal to terminal	5.5	mm
Comparative tracking index	CTI		>400	
Relative thermal index (electrical)	RTI	housing	140	°C

Table 2 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Stray inductance module	L_{SCE}			15		nH
Module lead resistance, terminals - chip	$R_{CC'+EE'}$	$T_H = 25^\circ\text{C}$, per switch		1.9		mΩ
Storage temperature	T_{stg}		-40		125	°C
Mounting torque for module mounting	M	- Mounting according to valid application note	M5, Screw	1.3	1.5	Nm
Weight	G			78		g

Note: The current under continuous operation is limited to 25A rms per connector pin.

2 IGBT, Inverter

Table 3 Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit
Collector-emitter voltage	V_{CES}	$T_{vj} = 25^\circ\text{C}$	1200	V
Continuous DC collector current	I_{CDC}	$T_{vj \text{ max}} = 175^\circ\text{C}$ $T_H = 40^\circ\text{C}$	200	A
Repetitive peak collector current	I_{CRM}	$t_p = 1 \text{ ms}$	400	A
Gate-emitter peak voltage	V_{GES}		±20	V

Table 4 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit	
			Min.	Typ.	Max.		
Collector-emitter saturation voltage	$V_{CE\ sat}$	$I_C = 200\ A, V_{GE} = 15\ V$	$T_{vj} = 25\ ^\circ C$		1.55	1.80	V
			$T_{vj} = 125\ ^\circ C$		1.69		
			$T_{vj} = 175\ ^\circ C$		1.77		
Gate threshold voltage	V_{GEth}	$I_C = 4.6\ mA, V_{CE} = V_{GE}, T_{vj} = 25\ ^\circ C$		5.15	5.80	6.45	V
Gate charge	Q_G	$V_{GE} = \pm 15\ V, V_{CE} = 600\ V$			3.34		μC
Internal gate resistor	R_{Gint}	$T_{vj} = 25\ ^\circ C$			0.75		Ω
Input capacitance	C_{ies}	$f = 100\ kHz, T_{vj} = 25\ ^\circ C, V_{CE} = 25\ V, V_{GE} = 0\ V$			40.3		nF
Reverse transfer capacitance	C_{res}	$f = 100\ kHz, T_{vj} = 25\ ^\circ C, V_{CE} = 25\ V, V_{GE} = 0\ V$			0.14		nF
Collector-emitter cut-off current	I_{CES}	$V_{CE} = 1200\ V, V_{GE} = 0\ V$	$T_{vj} = 25\ ^\circ C$			0.02	mA
Gate-emitter leakage current	I_{GES}	$V_{CE} = 0\ V, V_{GE} = 20\ V, T_{vj} = 25\ ^\circ C$				100	nA
Turn-on delay time (inductive load)	t_{don}	$I_C = 200\ A, V_{CE} = 600\ V, V_{GE} = \pm 15\ V, R_{Gon} = 2.7\ \Omega$	$T_{vj} = 25\ ^\circ C$		0.175		μs
			$T_{vj} = 125\ ^\circ C$		0.191		
			$T_{vj} = 175\ ^\circ C$		0.206		
Rise time (inductive load)	t_r	$I_C = 200\ A, V_{CE} = 600\ V, V_{GE} = \pm 15\ V, R_{Gon} = 2.7\ \Omega$	$T_{vj} = 25\ ^\circ C$		0.068		μs
			$T_{vj} = 125\ ^\circ C$		0.074		
			$T_{vj} = 175\ ^\circ C$		0.080		
Turn-off delay time (inductive load)	t_{doff}	$I_C = 200\ A, V_{CE} = 600\ V, V_{GE} = \pm 15\ V, R_{Goff} = 2.7\ \Omega$	$T_{vj} = 25\ ^\circ C$		0.351		μs
			$T_{vj} = 125\ ^\circ C$		0.413		
			$T_{vj} = 175\ ^\circ C$		0.454		
Fall time (inductive load)	t_f	$I_C = 200\ A, V_{CE} = 600\ V, V_{GE} = \pm 15\ V, R_{Goff} = 2.7\ \Omega$	$T_{vj} = 25\ ^\circ C$		0.107		μs
			$T_{vj} = 125\ ^\circ C$		0.194		
			$T_{vj} = 175\ ^\circ C$		0.264		
Turn-on energy loss per pulse	E_{on}	$I_C = 200\ A, V_{CE} = 600\ V, L_\sigma = 35\ nH, V_{GE} = \pm 15\ V, R_{Gon} = 2.7\ \Omega, di/dt = 2100\ A/\mu s (T_{vj} = 175\ ^\circ C)$	$T_{vj} = 25\ ^\circ C$		23.6		mJ
			$T_{vj} = 125\ ^\circ C$		34.9		
			$T_{vj} = 175\ ^\circ C$		39.5		
Turn-off energy loss per pulse	E_{off}	$I_C = 200\ A, V_{CE} = 600\ V, L_\sigma = 35\ nH, V_{GE} = \pm 15\ V, R_{Goff} = 2.7\ \Omega, dv/dt = 3250\ V/\mu s (T_{vj} = 175\ ^\circ C)$	$T_{vj} = 25\ ^\circ C$		13.8		mJ
			$T_{vj} = 125\ ^\circ C$		20.8		
			$T_{vj} = 175\ ^\circ C$		25.7		
SC data	I_{SC}	$V_{GE} \leq 15\ V, V_{CC} = 800\ V, V_{CEmax} = V_{CES} - L_{sCE} * di/dt$	$t_p \leq 8\ \mu s, T_{vj} = 150\ ^\circ C$		640		A
			$t_p \leq 7\ \mu s, T_{vj} = 175\ ^\circ C$		600		

(table continues...)

Table 4 (continued) Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Thermal resistance, junction to heat sink	R_{thJH}	per IGBT, $\lambda_{grease} = 3.3 \text{ W}/(\text{m}^2\text{K})$		0.331		K/W
Temperature under switching conditions	$T_{vj\text{op}}$		-40		175	°C

Note: $T_{vj\text{op}} > 150^\circ\text{C}$ is allowed for operation at overload conditions. For detailed specifications, please refer to AN 2018-14.

3 Diode, Inverter

Table 5 Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit	
Repetitive peak reverse voltage	V_{RRM}	$T_{vj} = 25^\circ\text{C}$	1200	V	
Continuous DC forward current	I_F		200	A	
Repetitive peak forward current	I_{FRM}	$t_p = 1 \text{ ms}$	400	A	
I^2t - value	I^2t	$V_R = 0 \text{ V}, t_p = 10 \text{ ms}$	$T_{vj} = 125^\circ\text{C}$	4150	A^2s
			$T_{vj} = 175^\circ\text{C}$	3800	

Table 6 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Forward voltage	V_F	$I_F = 200 \text{ A}, V_{GE} = 0 \text{ V}$	$T_{vj} = 25^\circ\text{C}$	1.72	2.10	V
			$T_{vj} = 125^\circ\text{C}$	1.59		
			$T_{vj} = 175^\circ\text{C}$	1.52		
Peak reverse recovery current	I_{RM}	$I_F = 200 \text{ A}, V_R = 600 \text{ V}, V_{GE} = -15 \text{ V}, -di_F/dt = 2100 \text{ A}/\mu\text{s} (T_{vj} = 175^\circ\text{C})$	$T_{vj} = 25^\circ\text{C}$	76.8		A
			$T_{vj} = 125^\circ\text{C}$	98.9		
			$T_{vj} = 175^\circ\text{C}$	115		
Recovered charge	Q_r	$I_F = 200 \text{ A}, V_R = 600 \text{ V}, V_{GE} = -15 \text{ V}, -di_F/dt = 2100 \text{ A}/\mu\text{s} (T_{vj} = 175^\circ\text{C})$	$T_{vj} = 25^\circ\text{C}$	14.5		μC
			$T_{vj} = 125^\circ\text{C}$	27.1		
			$T_{vj} = 175^\circ\text{C}$	33.1		
Reverse recovery energy	E_{rec}	$I_F = 200 \text{ A}, V_R = 600 \text{ V}, V_{GE} = -15 \text{ V}, -di_F/dt = 2100 \text{ A}/\mu\text{s} (T_{vj} = 175^\circ\text{C})$	$T_{vj} = 25^\circ\text{C}$	4.02		mJ
			$T_{vj} = 125^\circ\text{C}$	7.98		
			$T_{vj} = 175^\circ\text{C}$	10.5		

(table continues...)

Table 6 (continued) Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Thermal resistance, junction to heat sink	R_{thJH}	per diode, $\lambda_{grease} = 3.3 \text{ W}/(\text{m}^2\text{K})$		0.547		K/W
Temperature under switching conditions	$T_{vj\text{op}}$		-40		175	°C

Note: $T_{vj\text{op}} > 150^\circ\text{C}$ is allowed for operation at overload conditions. For detailed specifications, please refer to AN 2018-14.

4 NTC-Thermistor

Table 7 Characteristic values

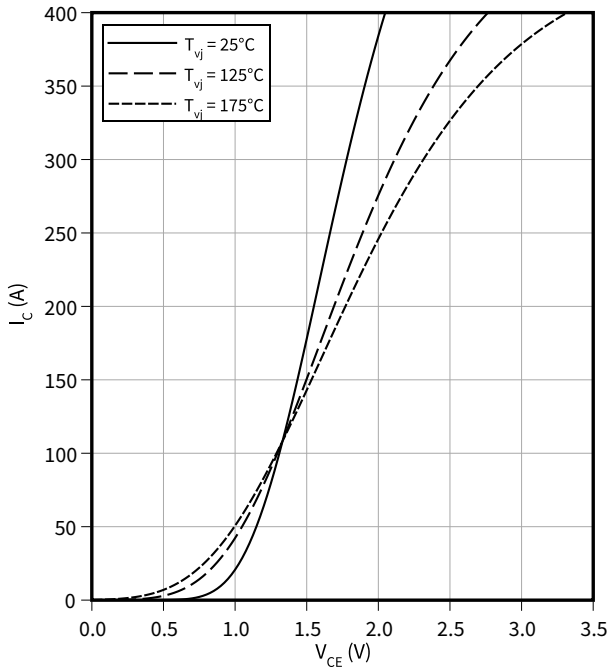
Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Rated resistance	R_{25}	$T_{NTC} = 25^\circ\text{C}$		5		kΩ
Deviation of R_{100}	$\Delta R/R$	$T_{NTC} = 100^\circ\text{C}$, $R_{100} = 493 \Omega$	-5		5	%
Power dissipation	P_{25}	$T_{NTC} = 25^\circ\text{C}$			20	mW
B-value	$B_{25/50}$	$R_2 = R_{25} \exp[B_{25/50}(1/T_2 - 1/(298,15 \text{ K}))]$		3375		K
B-value	$B_{25/80}$	$R_2 = R_{25} \exp[B_{25/80}(1/T_2 - 1/(298,15 \text{ K}))]$		3411		K
B-value	$B_{25/100}$	$R_2 = R_{25} \exp[B_{25/100}(1/T_2 - 1/(298,15 \text{ K}))]$		3433		K

Note: Specification according to the valid application note.

5 Characteristics diagrams

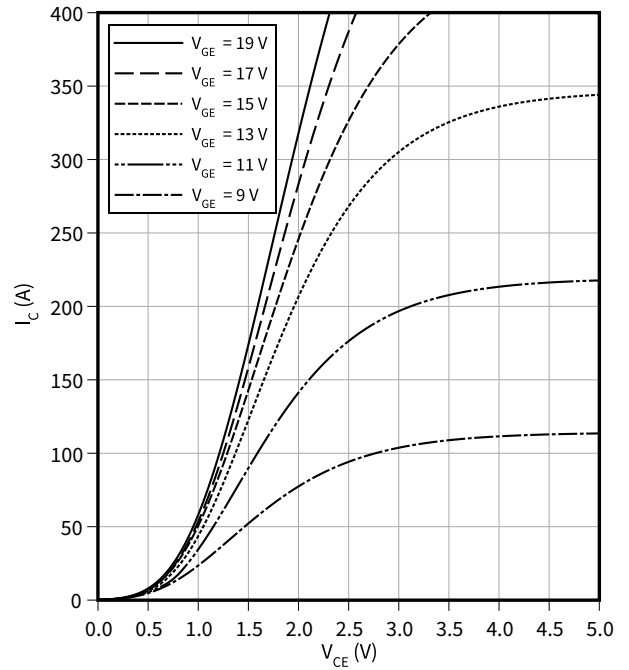
output characteristic (typical), IGBT, Inverter

$I_C = f(V_{CE})$
 $V_{GE} = 15\text{ V}$



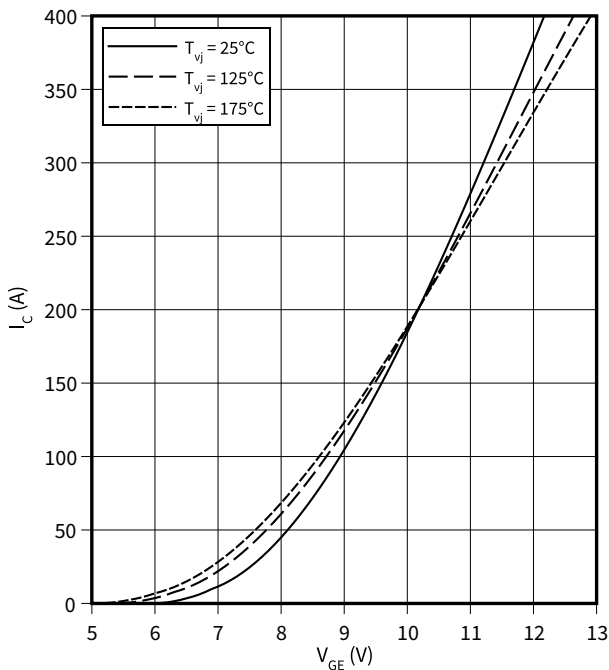
output characteristic (typical), IGBT, Inverter

$I_C = f(V_{CE})$
 $T_{vj} = 175\text{ °C}$



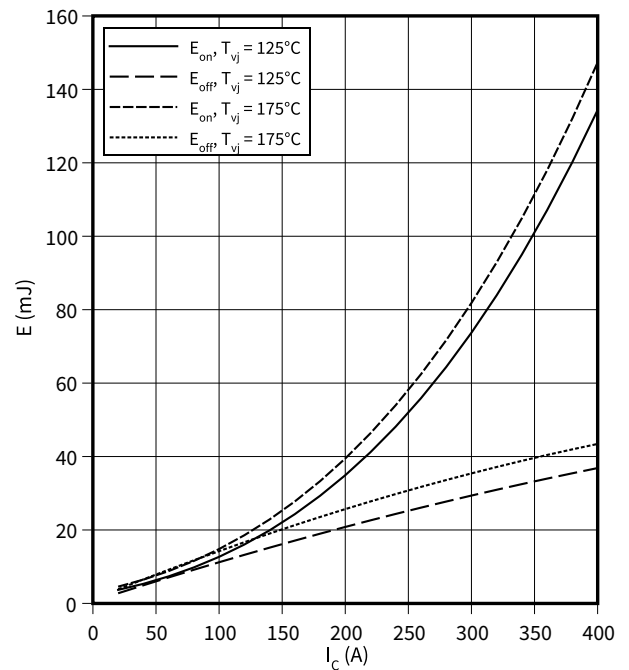
transfer characteristic (typical), IGBT, Inverter

$I_C = f(V_{GE})$
 $V_{CE} = 20\text{ V}$



switching losses (typical), IGBT, Inverter

$E = f(I_C)$
 $R_{Goff} = 2.7\ \Omega, R_{Gon} = 2.7\ \Omega, V_{CE} = 600\text{ V}, V_{GE} = \pm 15\text{ V}$

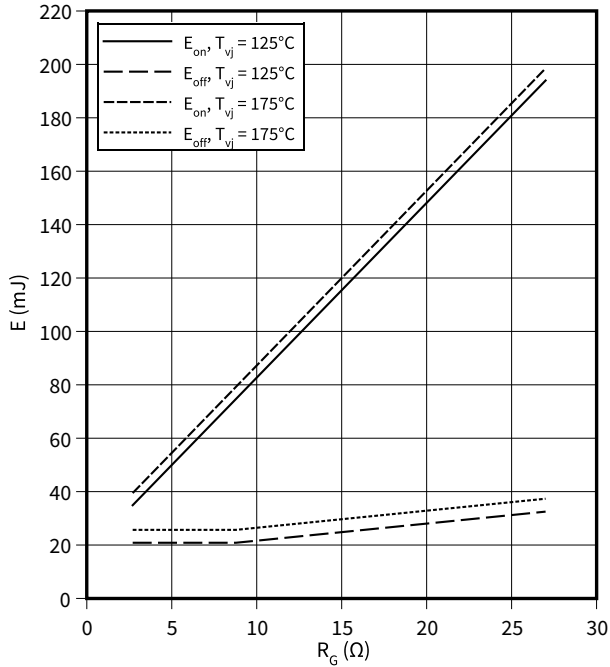


5 Characteristics diagrams

switching losses (typical), IGBT, Inverter

$E = f(R_G)$

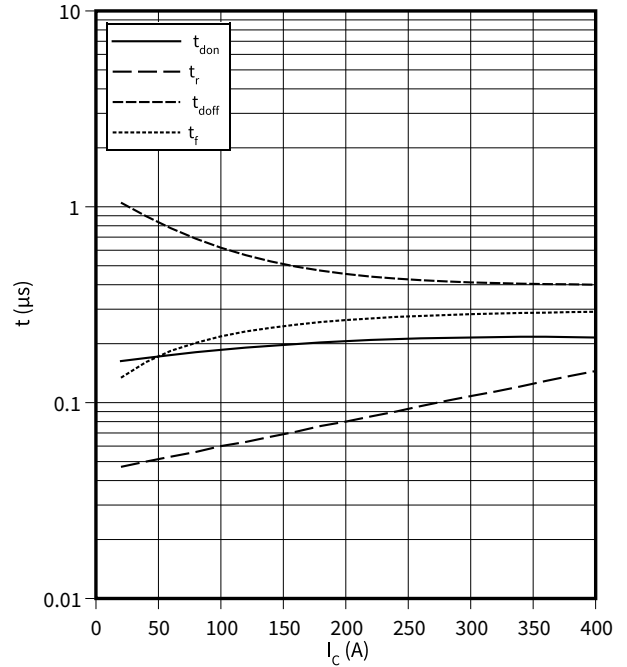
$I_C = 200 \text{ A}$, $V_{CE} = 600 \text{ V}$, $V_{GE} = \pm 15 \text{ V}$



switching times (typical), IGBT, Inverter

$t = f(I_C)$

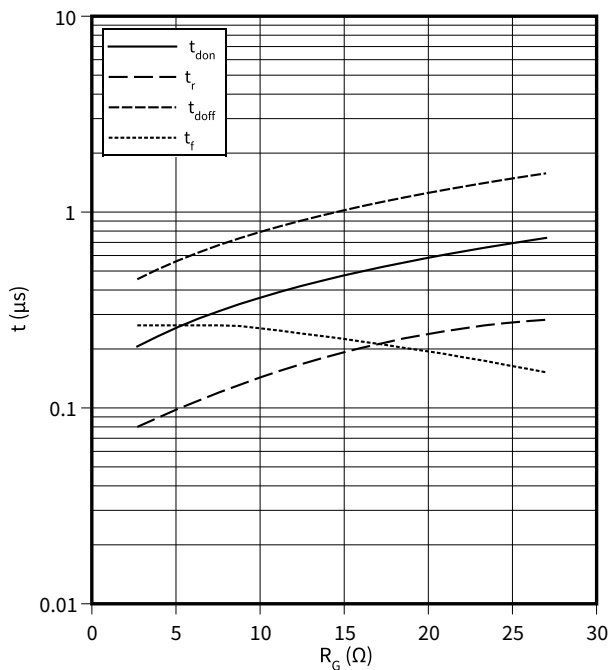
$R_{Goff} = 2.7 \Omega$, $R_{Gon} = 2.7 \Omega$, $V_{CE} = 600 \text{ V}$, $V_{GE} = \pm 15 \text{ V}$, $T_{vj} = 175 \text{ °C}$



switching times (typical), IGBT, Inverter

$t = f(R_G)$

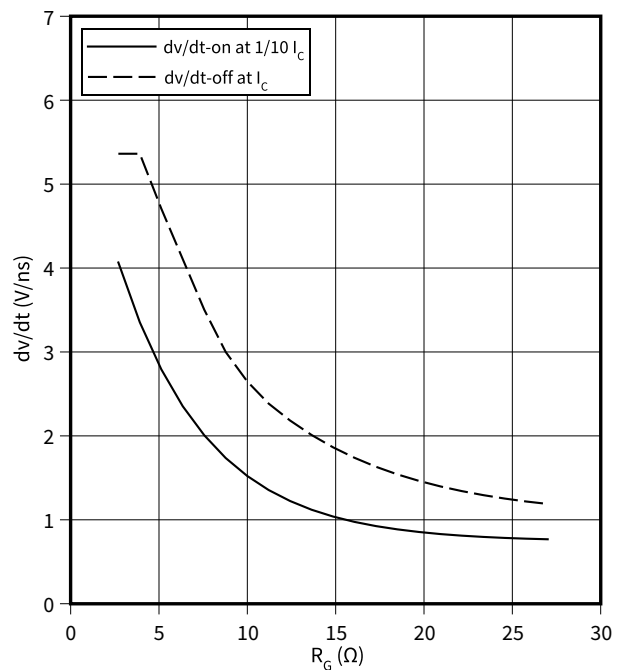
$I_C = 200 \text{ A}$, $V_{CE} = 600 \text{ V}$, $V_{GE} = \pm 15 \text{ V}$, $T_{vj} = 175 \text{ °C}$



Voltage slope (typical), IGBT, Inverter

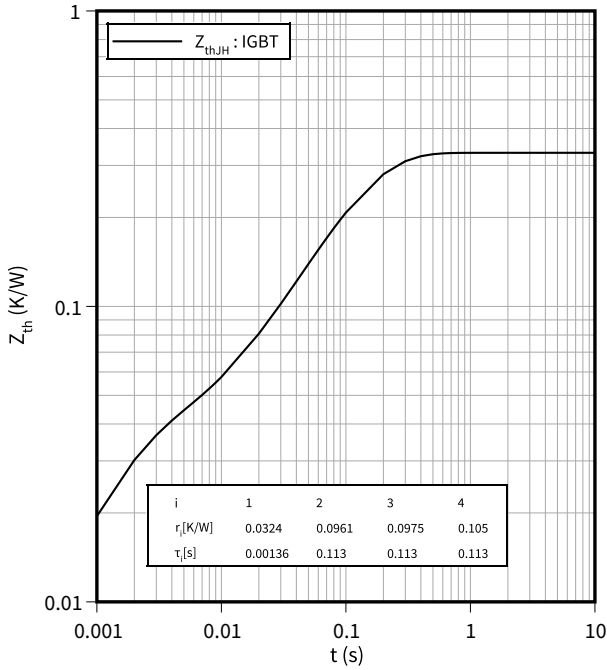
$dv/dt = f(R_G)$

$I_C = 200 \text{ A}$, $V_{CE} = 600 \text{ V}$, $V_{GE} = \pm 15 \text{ V}$, $T_{vj} = 25 \text{ °C}$



transient thermal impedance , IGBT, Inverter

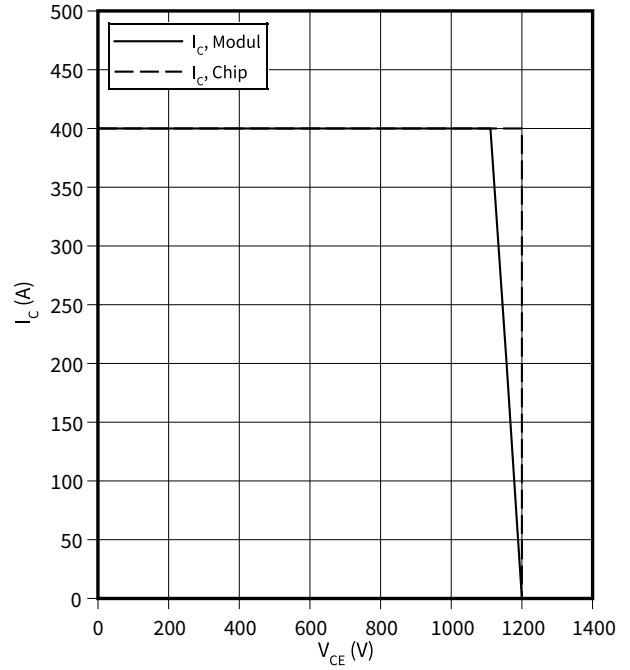
$Z_{th} = f(t)$



reverse bias safe operating area (RBSOA), IGBT, Inverter

$I_C = f(V_{CE})$

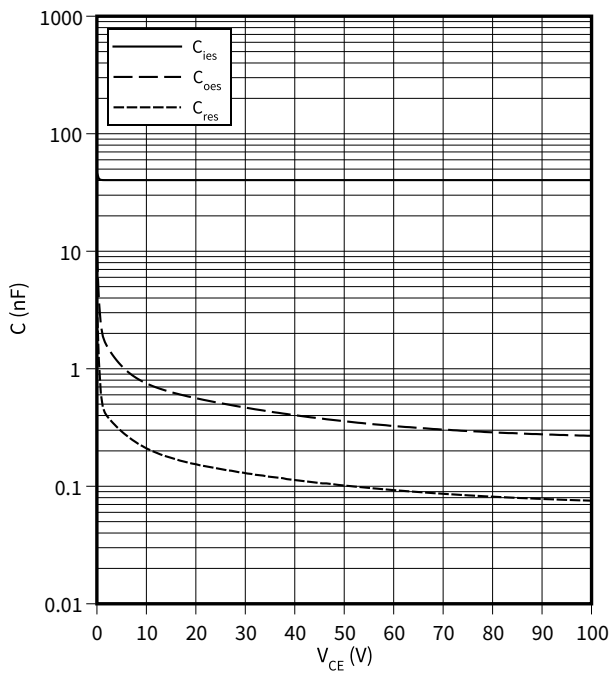
$R_{Goff} = 2.7 \Omega, V_{GE} = \pm 15 V, T_{vj} = 175 \text{ }^\circ\text{C}$



capacity characteristic (typical), IGBT, Inverter

$C = f(V_{CE})$

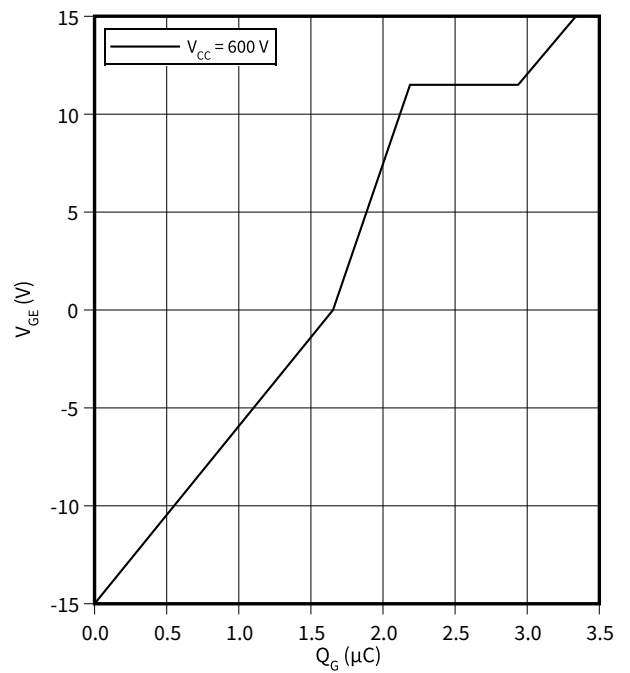
$f = 100 \text{ kHz}, V_{GE} = 0 V, T_{vj} = 25 \text{ }^\circ\text{C}$



gate charge characteristic (typical), IGBT, Inverter

$V_{GE} = f(Q_G)$

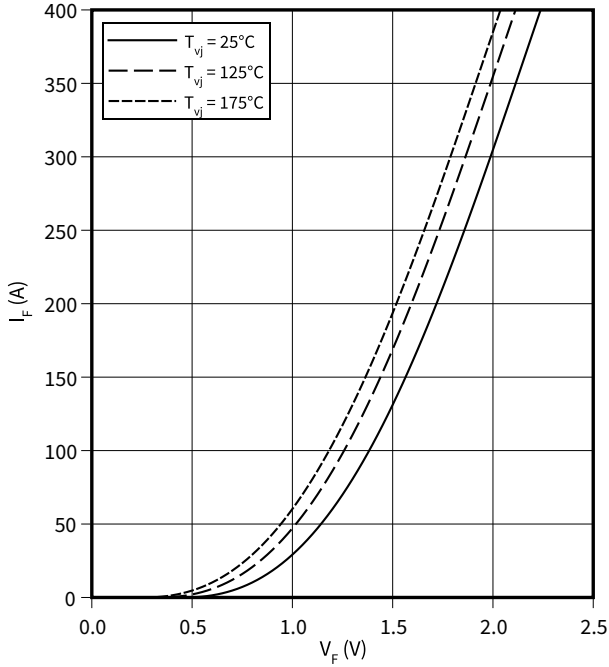
$I_C = 200 A, T_{vj} = 25 \text{ }^\circ\text{C}$



5 Characteristics diagrams

forward characteristic of (typical), Diode, Inverter

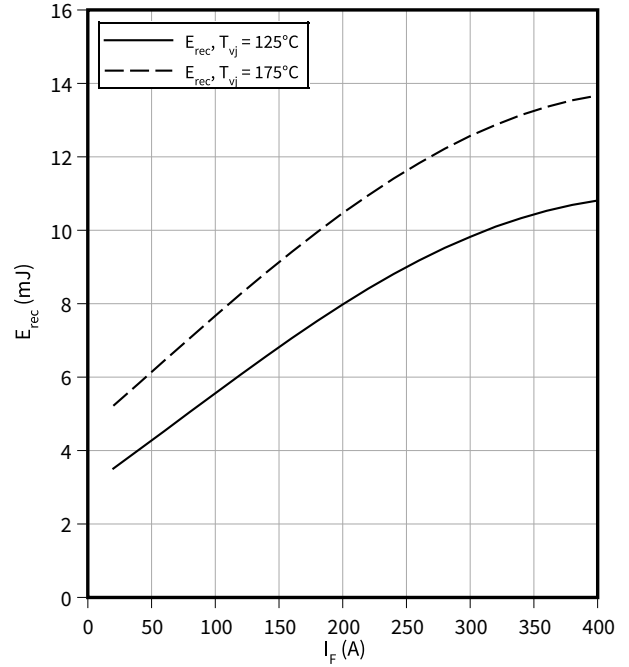
$I_F = f(V_F)$



switching losses (typical), Diode, Inverter

$E_{rec} = f(I_F)$

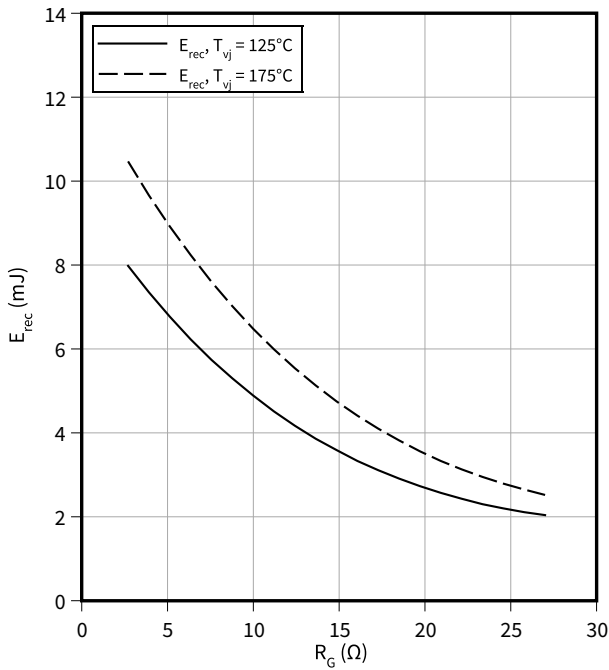
$R_G = 2.7 \Omega, V_R = 600 \text{ V}$



switching losses (typical), Diode, Inverter

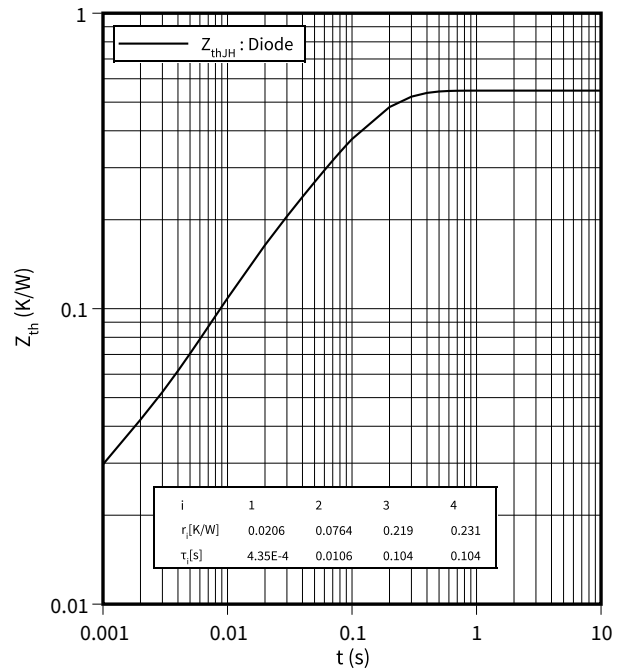
$E_{rec} = f(R_G)$

$I_F = 200 \text{ A}, V_R = 600 \text{ V}$



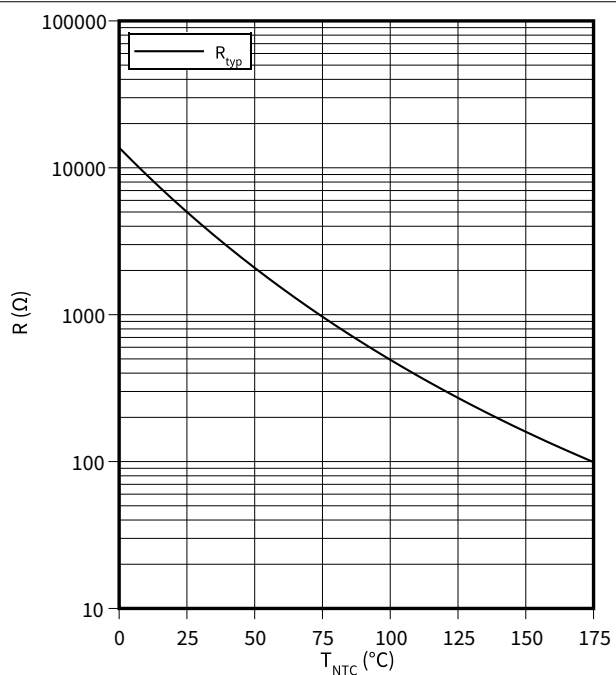
transient thermal impedance, Diode, Inverter

$Z_{th} = f(t)$



temperature characteristic (typical), NTC-Thermistor

$$R = f(T_{NTC})$$



6 Circuit diagram

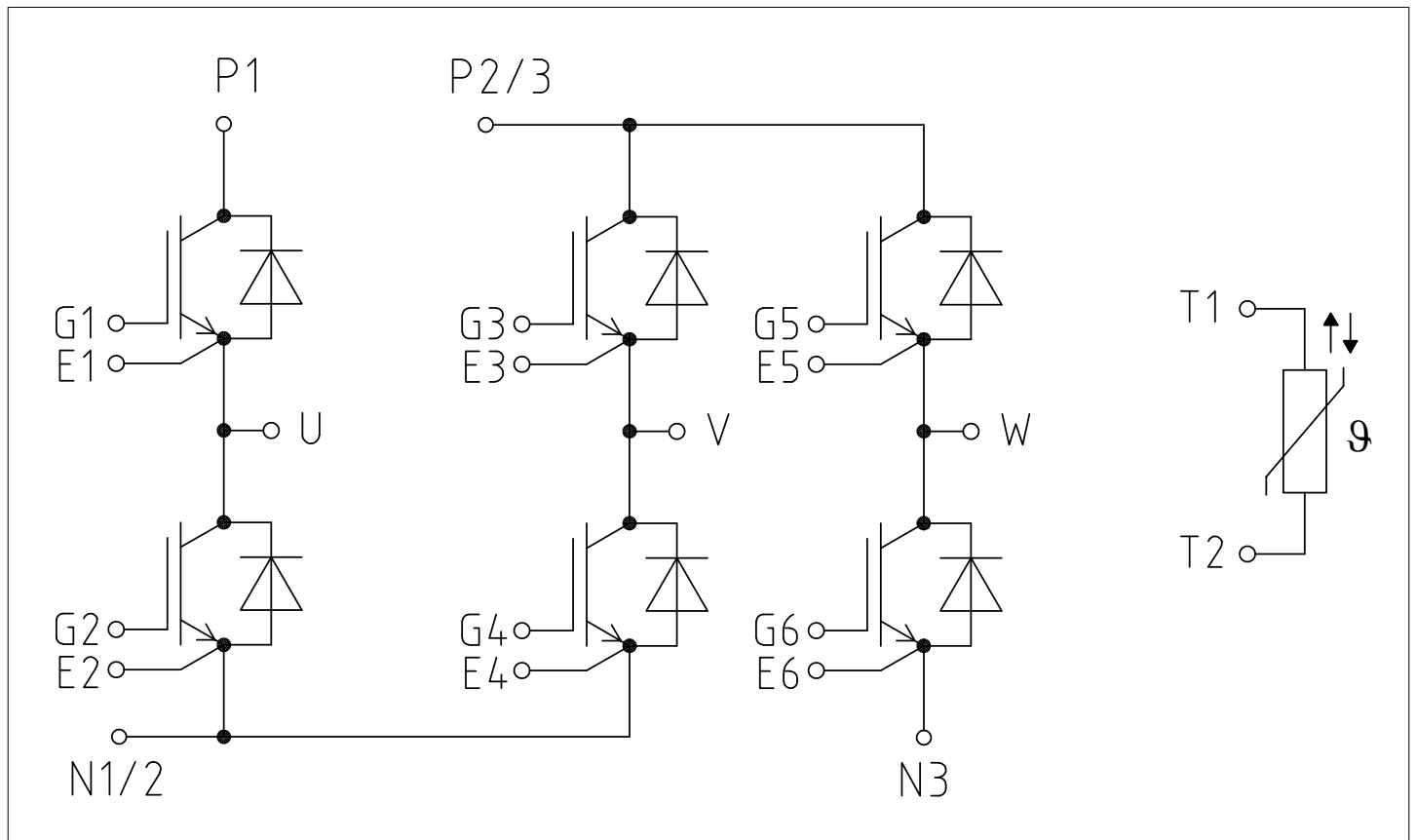


Figure 1

7 Package outlines

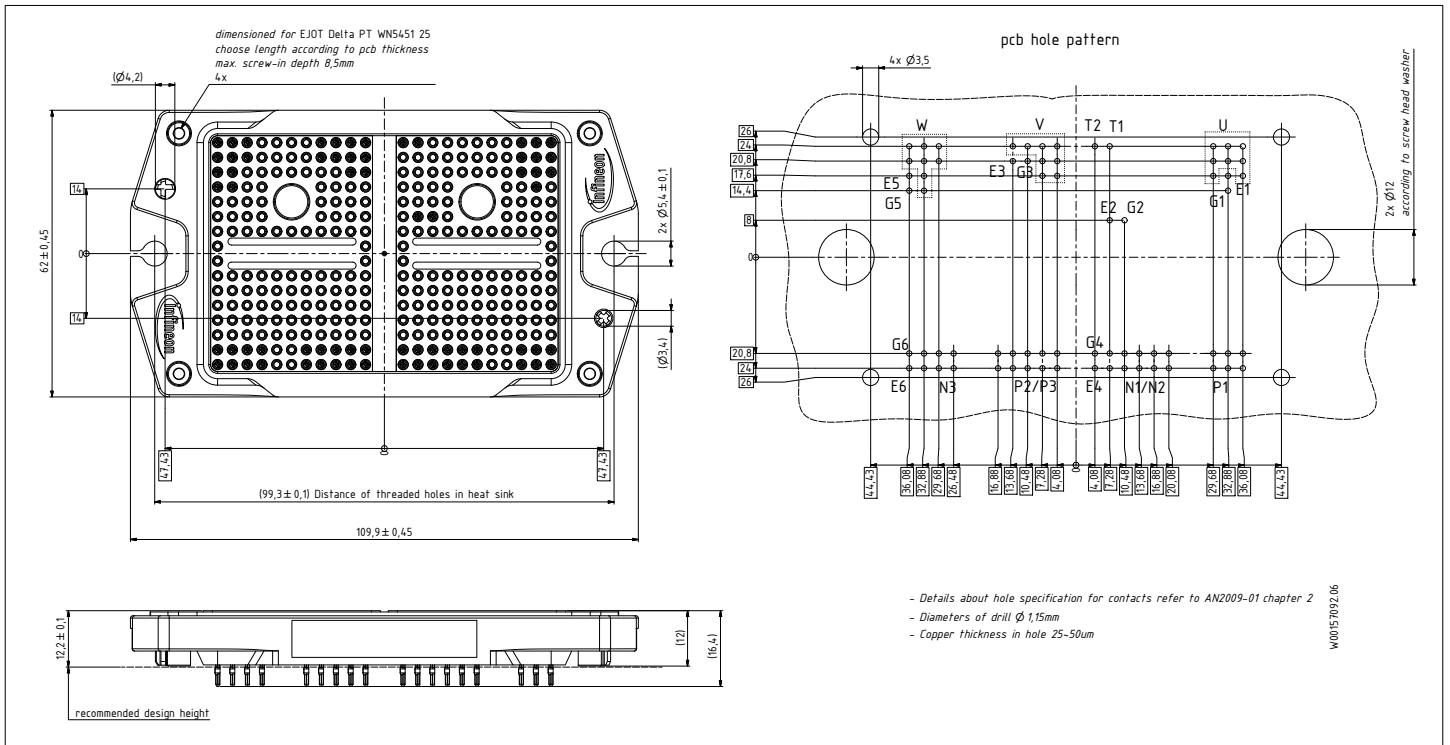


Figure 2

8 Module label code


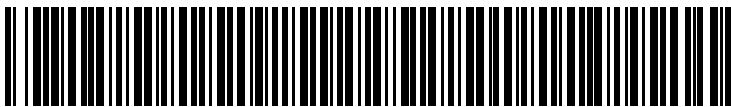
Module label code			
Code format	Data Matrix	Barcode Code128	
Encoding	ASCII text	Code Set A	
Symbol size	16x16	23 digits	
Standard	IEC24720 and IEC16022	IEC8859-1	
Code content	<i>Content</i>	<i>Digit</i>	<i>Example</i>
	Module serial number	1 - 5	71549
	Module material number	6 - 11	142846
	Production order number	12 - 19	55054991
	Date code (production year)	20 - 21	15
	Date code (production week)	22 - 23	30
Example	 		
	71549142846550549911530		

Figure 3

Revision history

Document revision	Date of release	Description of changes
V1.0	2019-09-11	Target datasheet
n/a	2020-09-01	Datasheet migrated to a new system with a new layout and new revision number schema: target or preliminary datasheet = 0.xy; final datasheet = 1.xy
1.00	2021-11-02	Final datasheet

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